

NEW ENGLAND SEMICONDUCTOR

POWER MOSFETS

N CHANNEL

TO-66

PACKAGE	DEVICE TYPE	BV_{DSS} VOLTS	$R_{DS(on)}$ @ 0.5 I_D OHMS	I_D Continuous AMPS	I_{DM} PULSE DRAIN CURRENT AMPS	P_D MAX WATTS
TO213AA (TO-66) 	NSFJ120	100	0.3	8.0	32	40
	NSFJ130	100	0.18	12.0	40	50
	NSFJ140	100	0.085	15.0	60	70
	NSFJ220	200	0.8	5.0	20	40
	NSFJ230	200	0.4	8.0	32	50
	NSFJ240	200	0.18	13.0	52	70
	NSFJ320	300	1.8	3.0	12	40
	NSFJ330	300	1.0	4.5	18	50
	NSFJ340	300	0.55	7.5	30	70
	NSFJ420	400	3.0	2.5	10	40
	NSFJ430	400	1.5	3.8	15	50
	NSFJ440	400	0.85	6.0	24	70
	NSFJ585	500	1.0	8.0	30	70
	NSFJ600	600	1.5	6.0	22	70
	NSFJ800	800	2.5	5.0	15	70
	NSFJ900	900	4.2	3.0	10	70
	NSFJ1000	1000	4.2	3.0	10	70

- Electrical Characteristics @ 25° C unless otherwise noted